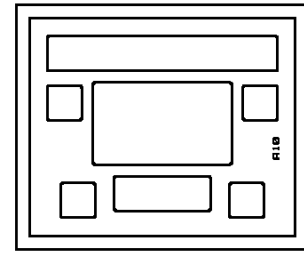


GD010**50V, DC – 8.0GHz, 10W GaN HEMT****FEATURES**

- Operating Frequency Range: DC to 8.0GHz
- Operating Drain Voltage: 28V & 50V
- Maximum Output Power (P_{SAT}): 15W
- Bare die shipped in Gel-Pak containers
- Suitable for CW, Pulsed, Linear applications
- 100% KGD DC Production Tested



0.90 x 0.75 mm Die

DESCRIPTION

The GD010 is a 15W (P3dB) unmatched discrete GaN-on-SiC HEMT which operates from DC to 8.0GHz on a 50V supply rail. The wide bandwidth of the GD010 makes it suitable for a variety of applications including cellular infrastructure, radar, communications, and test instrumentation, and can support CW, linear and pulse operations.

Bare die are shipped in Gel-Pak containers for safe transport and storage.

Typical Performances Measured Loadpull 1 Tone pulsed CW (10% duty cycle, 100 μ s width) in DFN 6x3 package, *2nd Harmonics NOT optimized*

- (1) Optimum Peak Power at 2.5dB in compression
- (2) Optimum Peak Efficiency at 2.5dB in compression

V_{ds}=50V, I_{dq}= 15 mA, T_A = 25°C

Frequency (MHz)	P _{out} ⁽¹⁾ (dBm)	Gain ⁽²⁾ (dB)	Eff ⁽²⁾ (%)
1000	41.4	21.9	58.3
1400	41.7	20.3	66
1800	41.6	19.6	60.2
2200	41.3	17.2	54.4
2600	41.6	18.4	57
3000	42	17.3	61.3
4000	42.1	16.6	64.8
5000	42	15	61
5500	41.7	13.8	58.8
6000	42	13.3	62.3

V_{ds}=28V, I_{dq}= 15 mA, T_A = 25°C

Frequency (MHz)	P _{out} ⁽¹⁾ (dBm)	Gain ⁽²⁾ (dB)	Eff ⁽²⁾ (%)
1000	38.9	20.4	63.7
1400	39.1	18.4	67.4
1800	39	16.9	67.6
2200	38.7	16.2	53.6
2600	39.1	16.2	58.7
3000	39.4	15.4	63.2
4000	39.4	14.9	66.5
5000	39.3	12.4	61.4
5500	39.1	11.7	61.7
6000	39.5	11	63.7

GD010

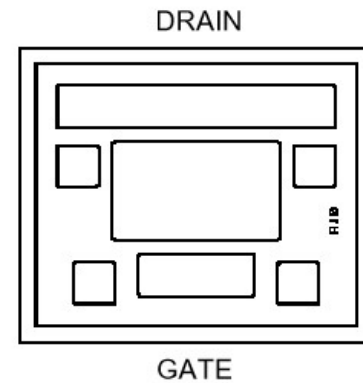
50V, DC – 8.0GHz, 10W GaN HEMT

ABSOLUTE MAXIMUM RATINGS^(1, 2)

Parameter	Rating	Symbols and Units
Drain Source Voltage	150	V_{DS} (V)
Gate Source Voltage	-8 to +2	V_{GS} (V)
Operating Voltage	55	V_{dsq} (V)
Junction Temperature	+225	T_{JUNC} (°C)
Storage Temperature	-65 to +150	$T_{STORAGE}$ (°C)

1. Exceeding any of these limits may cause permanent damage to this device or seriously limit the life time (MTTF)
2. GalliumSemi does not recommend sustained operation above maximum operating conditions.

BLOCK DIAGRAM

ELECTRICAL SPECIFICATIONS: $T_A = 25^\circ\text{C}$

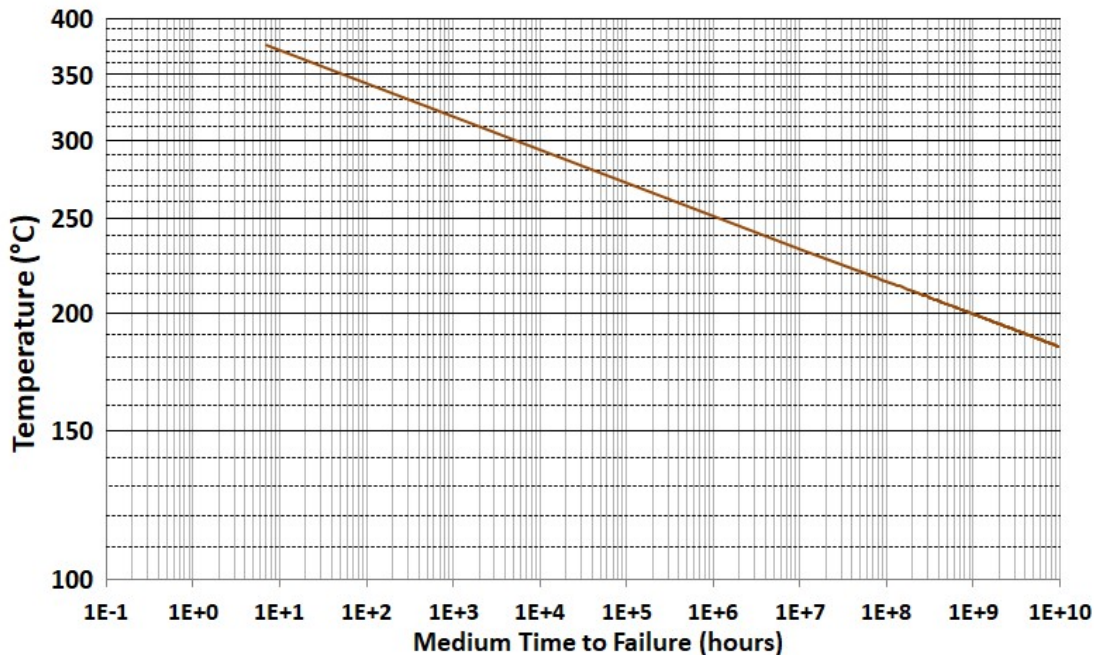
Parameter	Min.	Typ.	Max.	Symbols and Units	Test conditions
Frequency Range	DC		8000	MHz	
DC Characteristics					
Drain Source Breakdown Voltage	150			V_{BDSS} (V)	
Drain Source Leakage Current		0.65		I_{DLK} (mA)	$V_{gs} = -8\text{V}$, $V_{ds} = 50\text{V}$
Gate Threshold Voltage	-3.4		-1.5	V_{GS} (V)	$V_{ds} = 50\text{V}$
Operating Conditions					
Gate Bias Voltage		-2.5		V_{GSQ} (V)	
Drain Voltage		50		V_{DSQ} (V)	
Quiescent Drain Current		15		I_{DQ} (mA)	

GD010 **50V, DC – 8.0GHz, 10W GaN HEMT**

THERMAL AND RELIABILITY INFORMATION -CW ⁽¹⁾: T_c = 85°C

Parameter	Test condition	Value	Units	Notes
Channel Temperature, T _{ch}	P _{diss} 3 W	118.7	°C	
R _{th die}		7.4	°C/W	
MTTF		>1.0E+10	Hrs	
Channel Temperature, T _{ch}	P _{diss} 6 W	156.2	°C	
R _{th die}		8.4	°C/W	
MTTF		>1.0E+10	Hrs	
Channel Temperature, T _{ch}	P _{diss} 9 W	197.4	°C	
R _{th die}		8.6	°C/W	
MTTF		1.4E+09	Hrs	

Note 1. Assumes eutectic attach using 1mil low temp solder, mounted to a 8 mil DFN package.



GD010

50V, DC – 8.0GHz, 10W GaN HEMT

LOADPULL MEASUREMENT, Vds= 50V Idq = 15 mA

Die packaged in DFN 6x3, Measured 1 Tone Pulse CW, pulse width 100us, duty cycle 10%

For Optimum Peak Power @ 2.5dB Compression

Freq-MHz	Zin_F0	ZI_F0	Gain-dB	Pout-dBm	Pout-W	Eff-%	AMPM-deg
1000	6.8 j -32.6	48.2 j 15.0	22.6	41.4	14	53.8	-2.4
1200	7.3 j -27.8	45.1 j 15.1	20.8	41.7	14.9	56.3	-1.1
1400	6.8 j -22.2	43.2 j 31.1	20.6	41.7	15	63.3	-1.9
1600	6.6 j -19.7	42.7 j 23.3	19.9	41.8	14.9	53.7	2.2
1800	6.4 j -16.5	35.7 j 24.0	18.9	41.6	14.3	53.8	1.1
2000	6.6 j -14.3	42.6 j 27.1	17.1	41.2	13	49.1	-1.1
2200	5.7 j -12.5	38.6 j 24.3	16.8	41.3	13.4	45.9	1
2400	4.0 j -9.8	24.4 j 30.0	17.7	41.2	13.1	49.6	5.7
2600	3.5 j -8.6	27.3 j 21.4	17.7	41.6	14.5	48.7	4.1
2800	4.3 j -6.0	31.0 j 28.9	16.7	41.9	15.3	51.1	5.1
3000	3.5 j -3.7	28.9 j 22.4	17.2	42	15.7	52.3	2.5
3500	3.3 j 1.0	16.1 j 17.2	16	41.9	15.8	51.5	1.3
4000	3.7 j 6.6	15.6 j 18.5	15.3	42.1	16.4	58.6	0.1
4500	4.4 j 11.0	13.1 j 12.4	14.2	41.8	15.1	50.5	-0.6
5000	5.6 j 17.2	16.0 j 9.9	12.9	42	15.7	51.2	-0.5
5500	7.5 j 24.9	12.0 j 6.2	12.9	41.7	15	52.9	-1.1
6000	12.6 j 38.2	14.4 j 4.5	12.1	42	16.1	54.9	-0.1

For Optimum Peak Efficiency @ 2.5dB Compression

Freq-MHz	Zin_F0	ZI_F0	Gain-dB	Pout-dBm	Pout-W	Eff-%	AMPM-deg
1000	8.2 j -30.0	81.2 j 30.2	21.9	40.9	12.3	58.3	-1.7
1200	7.0 j -23.1	49.8 j 44.9	21.9	40.7	11.9	64.7	-2.9
1400	7.3 j -21.3	47.7 j 40.8	20.3	41.4	14.2	66	-0.6
1600	6.0 j -17.0	32.6 j 36.4	20.2	41.6	14.7	67.2	-2.6
1800	5.9 j -14.3	28.2 j 35.7	19.6	41.1	12.7	60.2	0
2000	6.2 j -12.2	29.8 j 39.8	18.1	40.3	11	54.1	-0.9
2200	5.3 j -11.1	27.8 j 33.7	17.2	41.1	13.1	54.4	2
2400	3.8 j -8.7	18.9 j 34.7	18.3	40.4	10.9	51	5.9
2600	3.6 j -6.1	19.0 j 36.4	18.4	40.7	11.6	57	6.1
2800	3.4 j -4.0	16.3 j 35.2	17.9	41.1	12.8	59.8	7.7
3000	3.4 j -2.0	21.8 j 37.3	17.3	41.4	13.7	61.3	6.1
3500	3.4 j 3.3	9.1 j 23.7	16.5	40.9	12.2	59.3	2.6
4000	3.2 j 8.9	7.9 j 20.1	16.6	40.7	12	64.8	0.3
4500	4.0 j 13.7	6.3 j 13.8	15.5	40.8	12.2	60	-1
5000	4.8 j 20.1	7.5 j 10.9	15	40.8	12.2	61	-2.2
5500	7.3 j 27.9	6.9 j 6.8	13.8	41	12.5	58.8	-1.6
6000	12.2 j 42.8	7.8 j 4.5	13.3	41.2	13.1	62.3	-1.5

GD010

50V, DC – 8.0GHz, 10W GaN HEMT

LOADPULL MEASUREMENT, $V_{ds}=28V$ $I_{dq}=15\text{ mA}$

Die packaged in DFN 6x3, Measured 1 Tone Pulse CW, pulse width 100us, duty cycle 10%

For Optimum Peak Power @ 2.5dB Compression

Freq-MHz	Zin_F0	ZI_F0	Gain-dB	Pout-dBm	Pout-W	Eff-%	AMPM-deg
1000	7.2 j -31.5	33.2 j 2.2	19.9	38.9	7.8	57.8	-3.8
1200	6.8 j -27.4	26.7 j 0.7	19.1	38.9	7.8	54.9	-1.9
1400	7.3 j -21.8	37.2 j 8.9	18.4	39.1	8.1	64.4	-1.8
1600	7.2 j -18.7	42.2 j 3.5	17	39	8	55.9	2.5
1800	7.3 j -15.6	39.1 j 8.1	16.2	39	8	56.3	2.7
2000	6.5 j -14.0	39.7 j 5.2	14.8	38.2	6.6	44.7	2.7
2200	5.5 j -11.5	39.2 j 9.8	14.8	38.7	7.4	48.8	4.2
2400	4.4 j -9.6	38.3 j 14.8	14.9	38.7	7.3	47.7	7.7
2600	3.5 j -7.4	31.8 j 13.9	16	39.1	8.1	53.2	5.6
2800	3.7 j -5.7	31.0 j 10.3	15	39.4	8.8	52.6	4
3000	3.5 j -2.6	34.3 j 14.3	14.9	39.4	8.7	57	3.1
3500	3.8 j 2.2	21.3 j 14.6	14.1	39.4	8.6	57	0.6
4000	3.7 j 6.8	22.8 j 8.0	13.5	39.4	8.7	55.3	-1.1
4500	4.8 j 12.9	15.4 j 11.8	12.1	39.3	8.4	57.7	-1.9
5000	6.7 j 18.0	23.9 j 5.6	11	39.3	8.5	51.6	-0.1
5500	8.0 j 26.1	19.7 j 2.4	10.7	39.1	8.2	53.3	-2.5
6000	12.1 j 40.2	23.2 j -1.7	10.3	39.5	8.9	55.3	-2.2

For Optimum Peak Efficiency @ 2.5dB Compression

Freq-MHz	Zin_F0	ZI_F0	Gain-dB	Pout-dBm	Pout-W	Eff-%	AMPM-deg
1000	7.6 j -28.3	53.8 j 9.7	20.4	38.3	6.8	63.7	-1.6
1200	8.4 j -21.0	59.5 j 36.1	19	36.7	4.8	66.3	1.6
1400	7.2 j -20.6	43.3 j 15.6	18.4	38.8	7.6	67.4	-0.8
1600	7.6 j -11.5	29.7 j 44.1	17.4	36.3	4.3	72	-2.8
1800	6.6 j -13.1	32.0 j 24.2	16.9	38.3	6.9	67.6	1.3
2000	5.9 j -11.7	36.6 j 32.1	15.7	37.3	5.4	48.7	6.7
2200	4.5 j -8.6	21.0 j 31.1	16.2	37.1	5.1	53.6	5.1
2400	3.6 j -8.3	26.2 j 27.4	16	38.1	6.4	52.4	8.9
2600	3.3 j -5.8	25.6 j 28.1	16.2	38.4	6.9	58.7	8.7
2800	2.9 j -3.5	20.3 j 25.2	16.7	38.4	6.9	61.1	5.7
3000	3.0 j -0.3	20.5 j 30.6	15.4	37.8	6	63.2	6
3500	3.2 j 4.7	10.6 j 19.1	14.6	37.8	6.1	63.9	2
4000	2.9 j 10.3	9.0 j 14.3	14.9	37.6	5.8	66.5	-1.9
4500	4.2 j 14.7	9.3 j 10.2	13.3	38.2	6.8	62.7	-2.8
5000	5.4 j 21.4	10.4 j 7.3	12.4	38	6.3	61.4	-3.9
5500	7.3 j 31.9	6.6 j 1.8	11.7	37	5	61.7	-6.8
6000	12.7 j 47.1	9.3 j -0.8	11	37.8	6.1	63.7	-4.9

GD010

50V, DC – 8.0GHz, 10W GaN HEMT

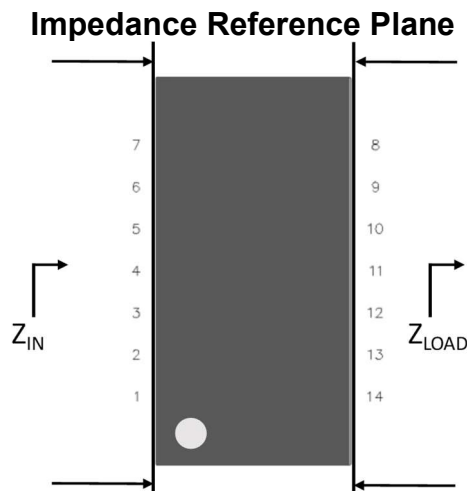
LOADPULL MEASUREMENT NOTES

Source and Load impedance @ 2nd Harmonic are set to 10 Ohms

With proper 2nd Harmonic termination, expect +5% Efficiency for Source and similar with Drain 2nd Harmonic.

Z_{LOAD} : Measured Impedance presented to the output of the device in the reference plane

Z_{IN} : Measured input Impedance at the input of the device in the reference plane

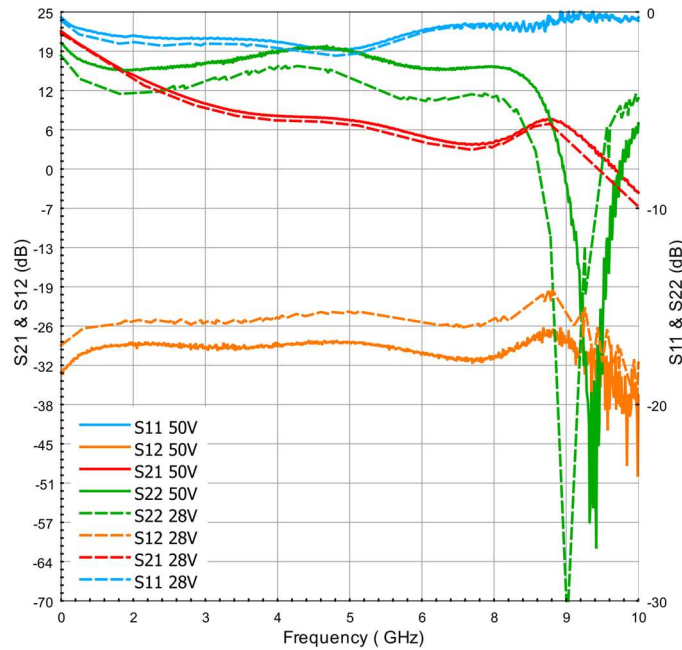


Raw data and full Loadpull measurement report available at request: sales@galliumsemi.com

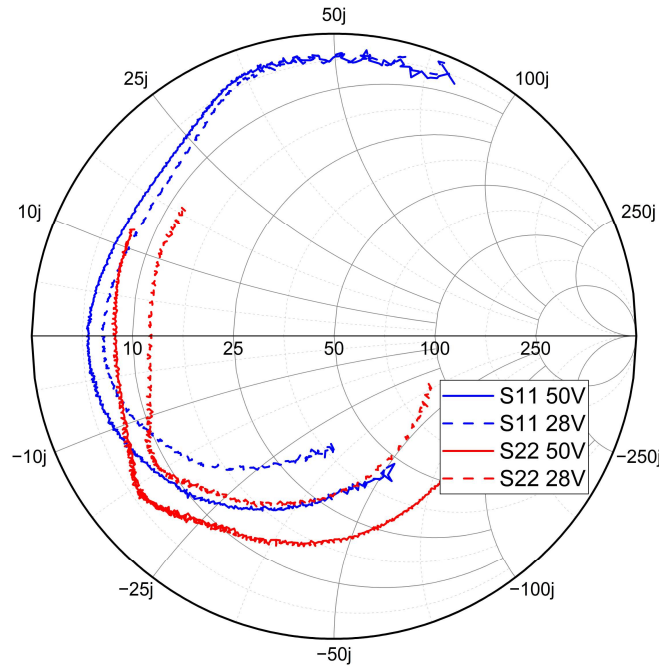
GD010 **50V, DC – 8.0GHz, 10W GaN HEMT**

BROADBAND S-PARAMETERS MEASUREMENT, $V_{ds}= 28 \text{ \& 50V}$ $I_{dq} = 15 \text{ mA}$
 Die packaged in DFN 6x3, Measured 1 Tone CW

S Parameters (Mag-dB)



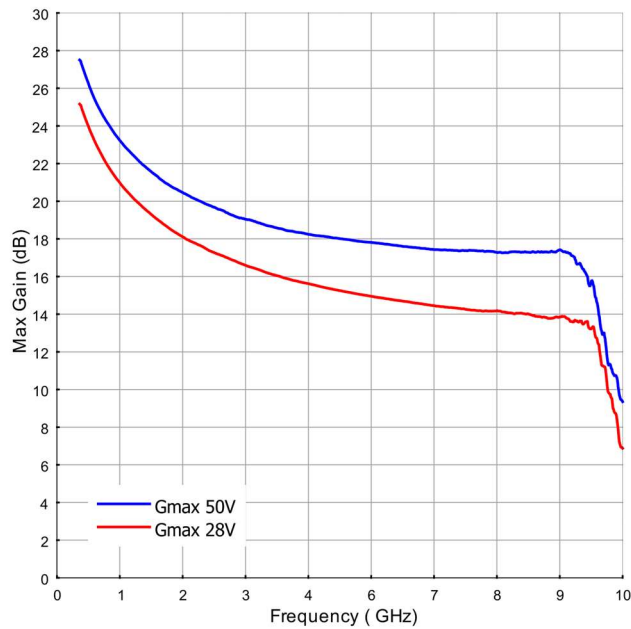
S11 & S22 0.4-8 GHz



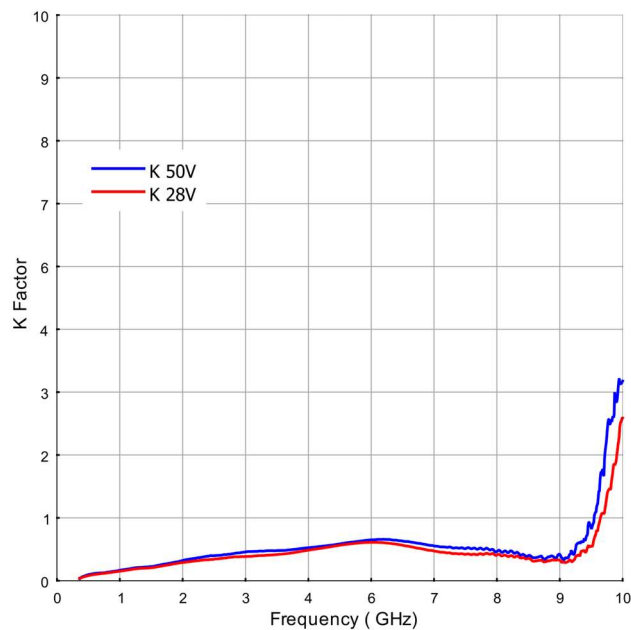
GD010 **50V, DC – 8.0GHz, 10W GaN HEMT**

BROADBAND S-PARAMETERS MEASUREMENT, $V_{ds} = 28$ & $50V$ $I_{dq} = 15$ mA
 Die packaged in DFN 6x3, Measured 1 Tone CW

Maximum Available Gain



K Factor



GD010**50V, DC – 8.0GHz, 10W GaN HEMT****GaN HEMT BIASING SEQUENCE**

To turn the transistor ON

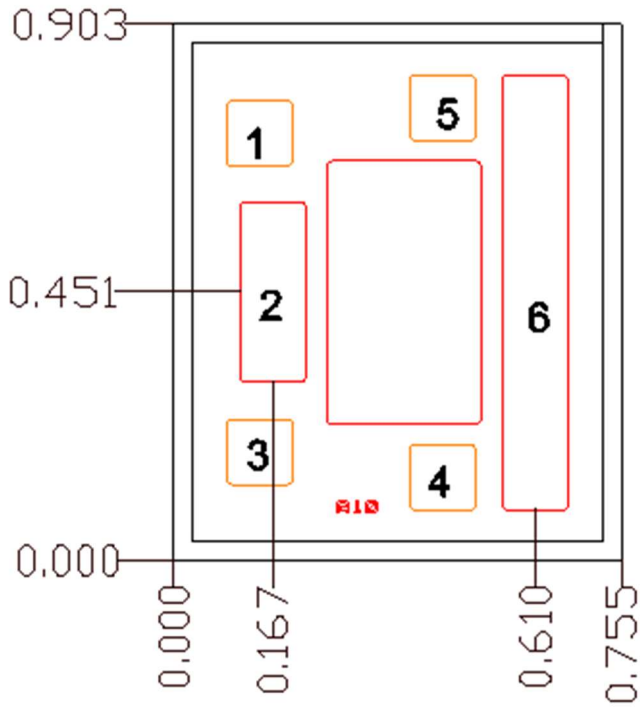
1. Set V_{GS} to -5V
2. Turn on V_{DS} to normal operation voltage (50V)
3. Slowly increase V_{GS} to set I_{DQ} current (16mA)
4. Apply RF power

To turn the transistor OFF

1. Turn the RF power off
2. Decrease V_{GS} to -1.5V
3. Turn off V_D . Wait a few seconds for drain capacitor to discharge
4. Turn off V_{GS}

GD010 **50V, DC – 8.0GHz, 10W GaN HEMT**

DIE DIMENSIONS



Bond Pads

Pad nb.	Description	Dimensions
1, 3, 4, 5	Not connected	
2, 6	RF Input / Gate Voltage	0.110 x 0.305
7	RF Output / Drain Voltage	0.110 x 0.733
Backside	Source/ Ground	0.755 x 0.903

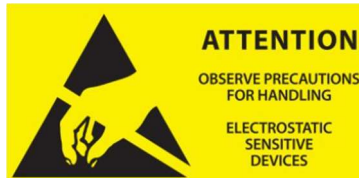
Notes:

1. All dimensions are in millimeter
2. Die thickness is 75 μ m
3. Bond pad metallization: gold
4. Backside metallization: gold

GD010**50V, DC – 8.0GHz, 10W GaN HEMT****HANDLING PRECAUTIONS**

Parameter	Symbol	Class	Test Methodology
ESD* – Human Body Model	HBM	Class 1A (250 V)	ANSI/ESDA/JEDEC Standard JS-001
ESD* – Charged Device Model	CDM	Class C3 (1500 V)	ANSI/ESDA/JEDEC Standard JS-002

* Tested in DFN 3x6 package



GD010

50V, DC – 8.0GHz, 10W GaN HEMT

CONTACT INFORMATION

To request latest information and samples, please contact us at:

Web: <https://www.galliumsemi.com/>

Email: sales@galliumsemi.com

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